Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
60V	2Ω @ V_{GS} = 4V	310mA
	2.5Ω @ V_{GS} = 2.5V	295mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

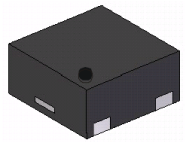
- DC-DC converters
- Power management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

Mechanical Data

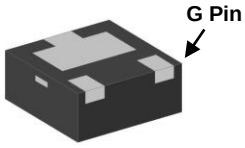
- Package: U-DFN1212-3
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

ESD PROTECTED

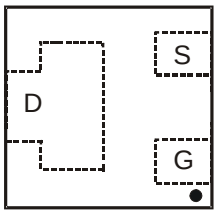
U-DFN1212-3 (Type C)



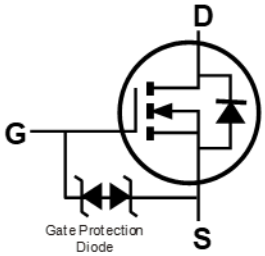
Top View



Bottom View



Pin-Out Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN62D0LFD-7	U-DFN1212-3 (Type C)	3,000	Tape & Reel
DMN62D0LFD-13	U-DFN1212-3 (Type C)	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

K63 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: J = 2022)
M = Month (ex: 9 = September)

Date Code Key

Year	2013	…	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	A	…	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 4.0V	T_A = +25°C T_A = +70°C	I_D	310 260	mA
Pulsed Drain Current (Note 6) (10µs Pulse, Duty Cycle = 1%)		I_{DM}	1.0	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P_D	0.48	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	265	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±5V, V_{DS} = 0V
		—	—	±500	nA	V_{GS} = ±10V, V_{DS} = 0V
		—	—	±2.0	µA	V_{GS} = ±15V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	—	1.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	1.3	2	Ω	V_{GS} = 4V, I_D = 100mA
		—	1.4	2.5		V_{GS} = 2.5V, I_D = 50mA
		—	1.8	3		V_{GS} = 1.8V, I_D = 50mA
		—	2.4	—		V_{GS} = 1.5V, I_D = 10mA
Forward Transfer Admittance	$\|Y_{fs}\|$	—	1.8	—	S	V_{DS} = 10V, I_D = 200mA
Diode Forward Voltage	V_{SD}	—	0.8	1.3	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	31	—	pF	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	4.3	—		
Reverse Transfer Capacitance	C_{rss}	—	3.0	—		
Gate Resistance	R_g	—	99	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	0.5	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	0.09	—		
Gate-Drain Charge	Q_{gd}	—	0.07	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.6	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_L = 150Ω, R_G = 25Ω, I_D = 200mA
Turn-On Rise Time	t_R	—	2.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—	ns	
Turn-Off Fall Time	t_F	—	8.7	—	ns	

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Repetitive rating, pulse width limited by junction temperature.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

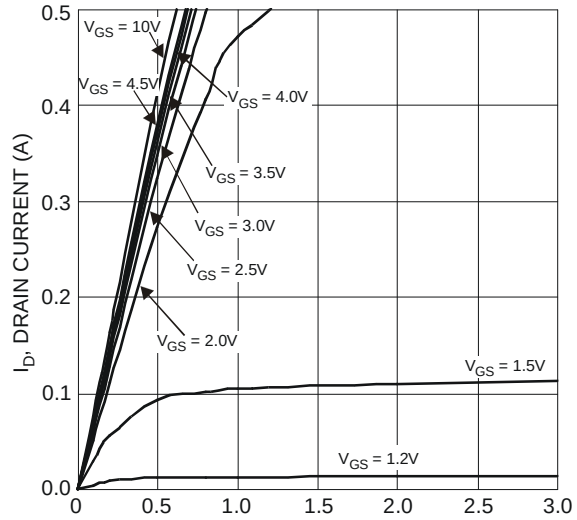


Figure 1 Typical Output Characteristics

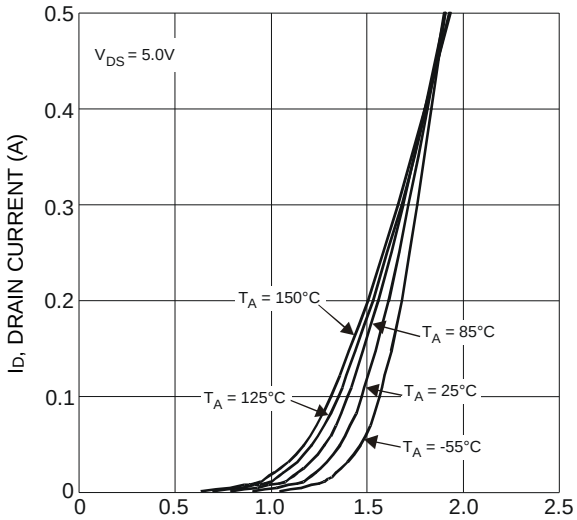


Figure 2 Typical Transfer Characteristics

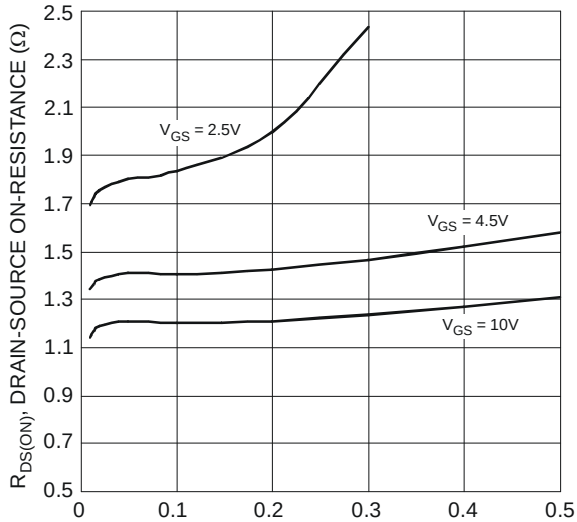


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

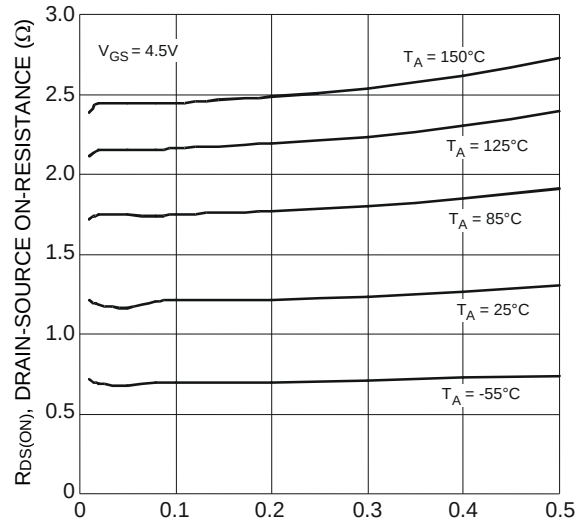


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

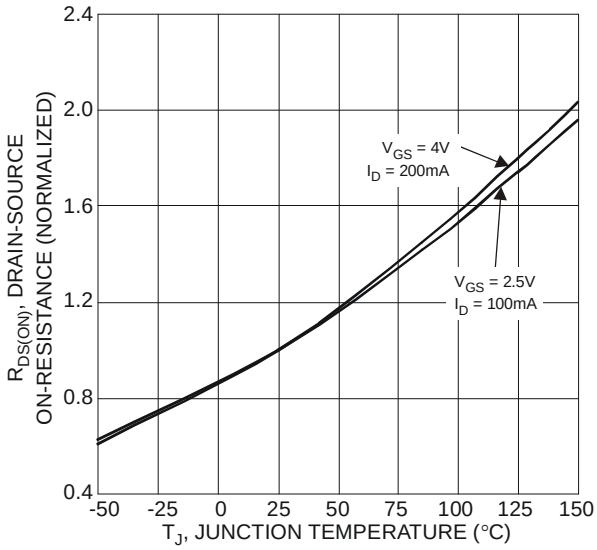


Figure 5 On-Resistance Variation with Temperature

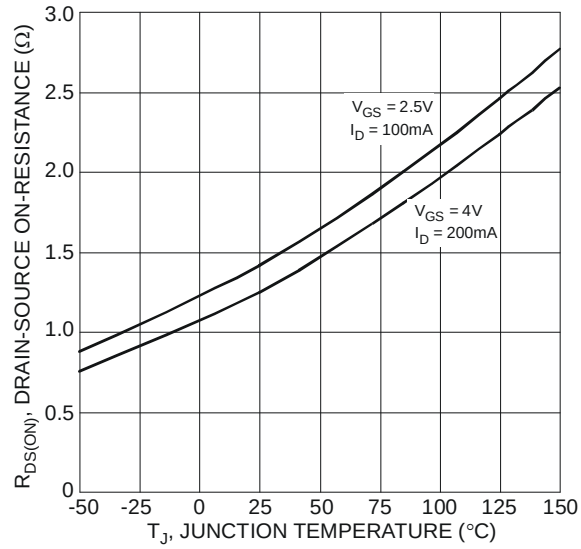


Figure 6 On-Resistance Variation with Temperature

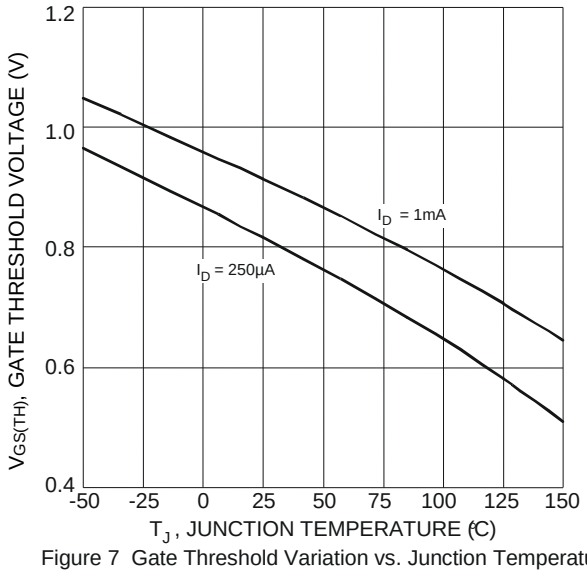


Figure 7 Gate Threshold Variation vs. Junction Temperature

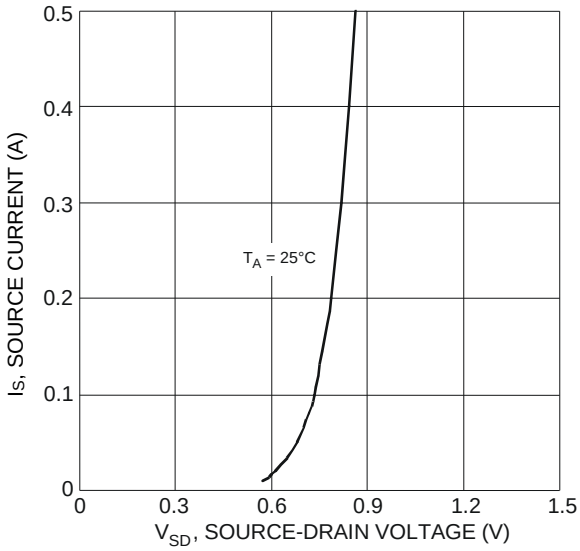


Figure 8 Diode Forward Voltage vs. Current

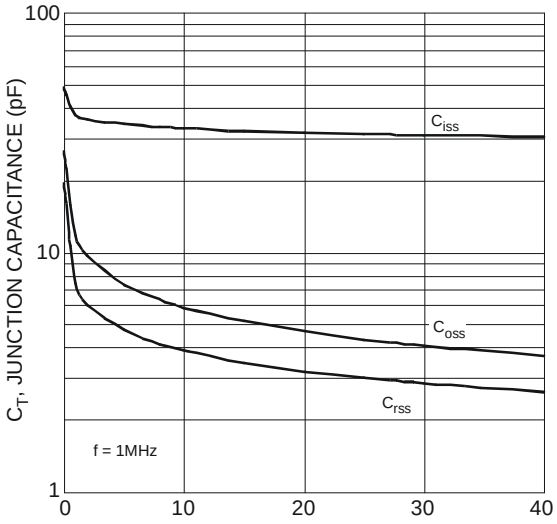


Figure 9 Typical Junction Capacitance

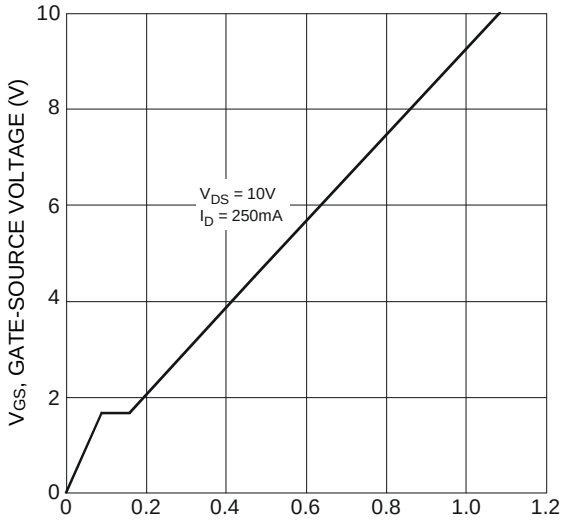


Figure 10 Gate Charge

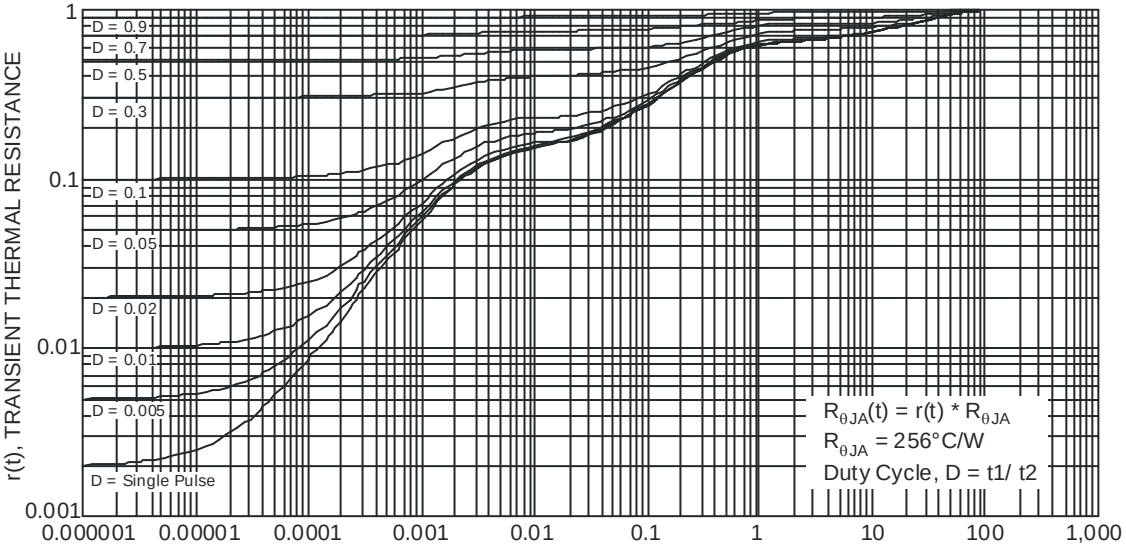
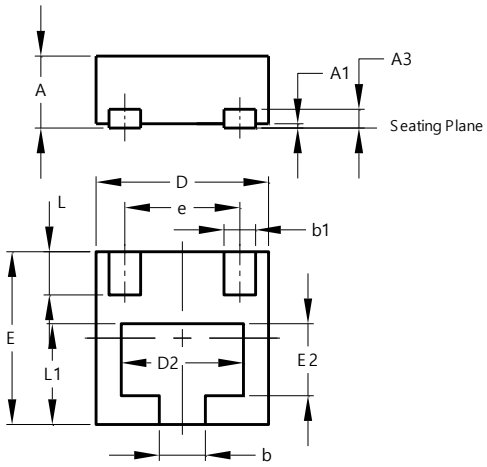


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1212-3 (Type C)

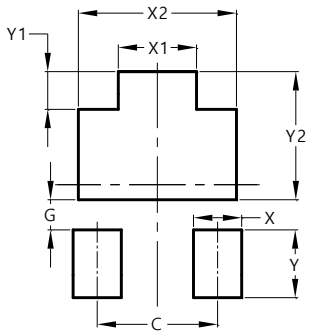


U-DFN1212-3 Type C			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
D2	0.75	0.95	0.85
e	-	-	0.80
E	1.15	1.25	1.20
E2	0.40	0.60	0.50
L	0.25	0.35	0.30
L1	0.65	0.75	0.70
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN1212-3 (Type C)



Dimensions	Value (in mm)
C	0.800
G	0.200
X	0.320
X1	0.520
X2	1.050
Y	0.450
Y1	0.250
Y2	0.850

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